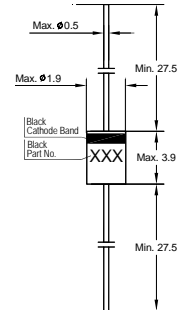


Features

- Fast switching speed
- High reliability



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Current	$I_{F(AV)}$	200	mA
Peak Forward Surge Current	I_{FSM}	1 4	A
		at $t = 1\text{ s}$ at $t = 1\text{ }\mu\text{s}$	
Total Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 200	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	100 75	- -	V
Reverse Current	I_R	- - -	25 5 50	nA μA μA
Reverse Current				at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}, T_j = 150\text{ }^\circ\text{C}$
Forward Voltage	V_F	0.63	0.73	V
Forward Voltage	V_F	-	1	V
Forward Voltage	V_F	-	1	V
Forward Voltage	V_F	-	1	V
Total Capacitance	C_T	-	2	pF
Reverse Recovery Time	t_{rr}	-	4	ns
Reverse Recovery Time				at $I_F = 10\text{ mA}, V_R = 6\text{ V (60 mA)}, I_{RR} = 1\text{ mA}, R_L = 100\text{ }\Omega$

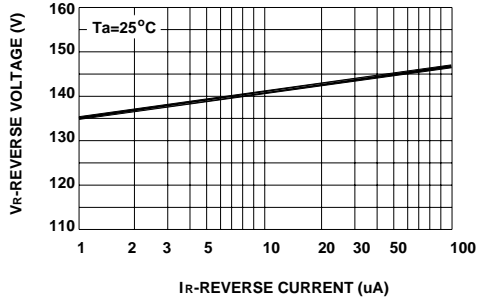
Zibo Seno Electronic Engineering Co., Ltd.



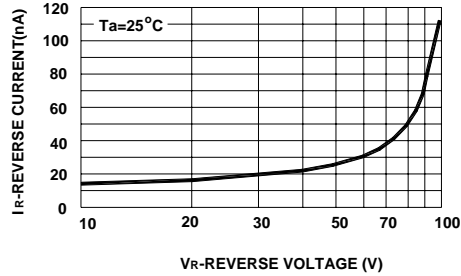
1N916 1N916A 1N916B



REVERSE VOLTAGE vs REVERSE CURRENT
BV-1.0 to 100 μ A

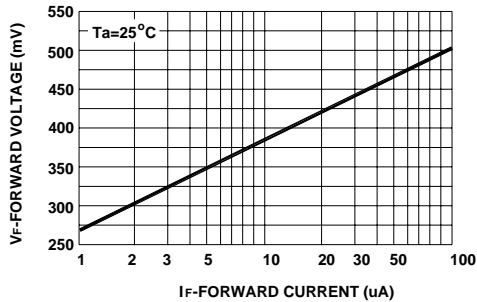


REVERSE CURRENT vs REVERSE VOLTAGE
IR-10 to 100 V

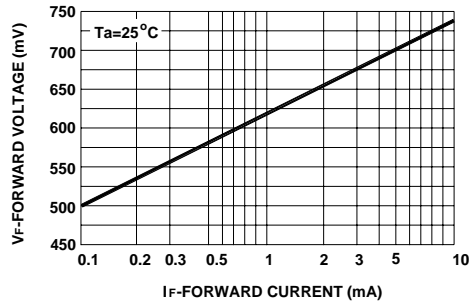


GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

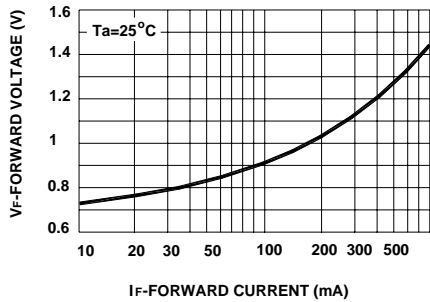
FORWARD VOLTAGE vs FORWARD CURRENT
Vf-1 to 100 μ A



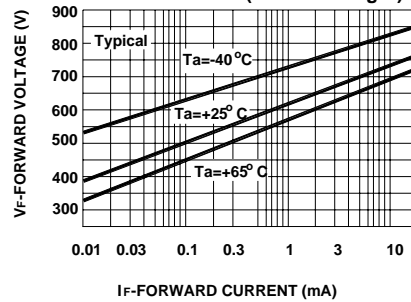
FORWARD VOLTAGE vs FORWARD CURRENT
Vf-0.1 to 100 mA



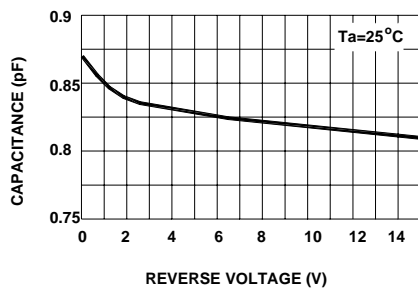
FORWARD VOLTAGE vs FORWARD CURRENT
Vf-10 to 800 mA



FORWARD VOLTAGE vs AMBIENT TEMPERATURE
Vf-0.01 - 20 mA (-40 to +65 Deg C)



CAPACITANCE vs REVERSE VOLTAGE
VR=0.0 to 15 V



REVERSE RECOVERY TIME vs REVERSE CURRENT

